

## NTE26 Silicon NPN Transistor Low Noise Audio Amplifier

**Features:**

- $V_{CEO} = 120V$  (Min)
- Low Noise: = 1dB (Typ), 10dB (Max)

**Absolute Maximum Ratings:** ( $T_A = +25^{\circ}C$  unless otherwise specified)

Collector–Base Voltage, $V_{CBO}$ .....	120V
Collector–Emitter Voltage, $V_{CEO}$ .....	120V
Emitter–Base Voltage, $V_{EBO}$ .....	5V
Collector Current, $I_C$ .....	100mA
Emitter Current, $I_E$ .....	–100mA
Collector Dissipation, $P_C$ .....	200mW
Operating Junction Temperature, $T_J$ .....	+125°C
Storage Temperature Range, $T_{stg}$ .....	–55° to +125°C

**Electrical Characteristics:** ( $T_A = +25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 120V, I_E = 0$	–	–	0.1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$	–	–	0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = 6V, I_C = 2mA$	350	–	700	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$	–	–	0.3	V
Current Gain–Bandwidth Product	$f_T$	$V_{CE} = 6V, I_C = 1mA$	–	100	–	MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$	–	3.0	–	pF
Noise	NF	$V_{CE} = 6V, I_C = 0.1mA, f = 1kHz,$ $r_g = 10k\Omega$	–	1.0	10	dB

